

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 57810-084		SERIAL NO. Divisional of Appl No. 10/084,050	
				APPLICANT Nobuhiko HAYASHI, et al.			
				FILING DATE March 10, 2004		GROUP	

U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
De De		US 6,015,979	1/18/2000	Sugiura et al.			
		US 6,051,849	4/18/2000	Davis et al.			
		US 6,503,769	01/07/2003	Nakamura et al.			
		US					
		US					

FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes - Number - Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
De De		2000-164989	6/16/2000			Yes	No
		2000-269144	9/29/2000			Japan (w/ English Abstract)	
		2000-21789	1/21/2000			Japan (w/ English Abstract)	
		10-312971	11/24/1998			Japan (w/ English Abstract)	

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
De De		S. Nakamura et al., "Long lifetime violet InGaN/GaN/AlGaIn-based semiconductor lasers", Journal of Oyo Denshi Bussai Bunkakai, Vol. 4, (1998), pp. 53-58 and 210-215.	
		Akira Usui et al., "Thick GaN Epitaxial Growth with Low Dislocation Density by Hydride Vapor Phase Epitaxy", Jpn. J. Appl. Phys. Vol. 36 (1997), pp. L899-L902.	
		Kevin Linthicum et al., "Pendeoepitaxy of gallium nitride thin films", Applied Physics Letter, Vol. 75, No. 2, July 12, 1999, pp. 196-198.	
		Isao Kidoguchi et al., "Air-bridged lateral epitaxial overgrowth of GaN thin films", Applied Physics Letter, Vol. 76, No. 25, June 18, 2000, pp. 3768-3770.	

EXAMINER De	DATE CONSIDERED 12/2005
--	--

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.